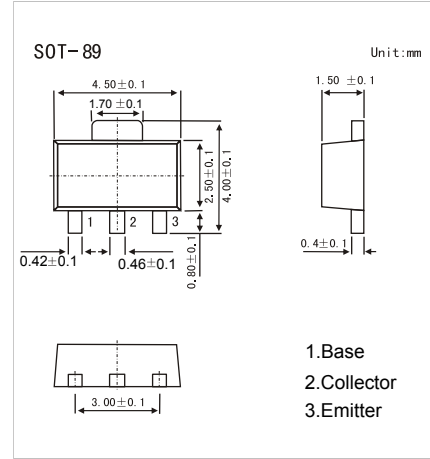


NPN Transistors

2SD2150

■ Features

- Excellent current-to-gain characteristics
- Low collector saturation voltage $V_{CE(sat)}$
- Complementary to 2SB1412



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	40	V
Collector - Emitter Voltage	V_{CEO}	20	
Emitter - Base Voltage	V_{EBO}	6	
Collector Current - Continuous	I_C	3	A
Collector Power Dissipation	P_C	500	mW
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 to 150	

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	$I_C = 100\mu\text{A}, I_E = 0$	40			V
Collector- emitter breakdown voltage	V_{CEO}	$I_C = 1\text{mA}, I_B = 0$	20			
Emitter - base breakdown voltage	V_{EBO}	$I_E = 100\mu\text{A}, I_C = 0$	6			
Collector-base cut-off current	I_{CBO}	$V_{CB} = 35\text{V}, I_E = 0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 5\text{V}, I_C = 0$			0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 2\text{A}, I_B = 100\text{mA}$			0.5	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = 2\text{A}, I_B = 100\text{mA}$			1.2	
DC current gain	h_{FE}	$V_{CE} = 2\text{V}, I_C = 100\text{mA}$	180		560	
Collector output capacitance	C_{ob}	$V_{CB} = 10\text{V}, I_E = 0, f = 1\text{MHz}$		25		pF
Transition frequency	f_T	$V_{CE} = 2\text{V}, I_C = 500\text{mA}, f = 100\text{MHz}$		290		MHz

■ Classification of h_{FE}

Type	2SD2150-R	2SD2150-S
Range	180-390	270-560
Marking	CF R*	CF S*



炬芯微
XUANXINWEI

SMD Type

Transistors

NPN Transistors

2SD2150

Typical Characteristics

